

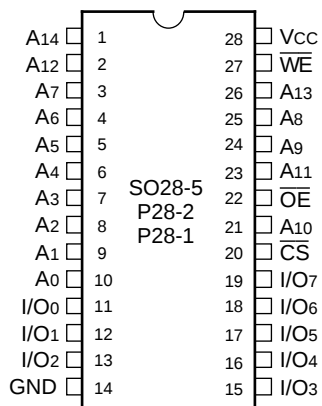
IDT71256SA

The IDT71256SA is packaged in 28-pin 300- and 600-mil Plastic DIP, 28-pin 300 mil Plastic SOJ and TSOP.

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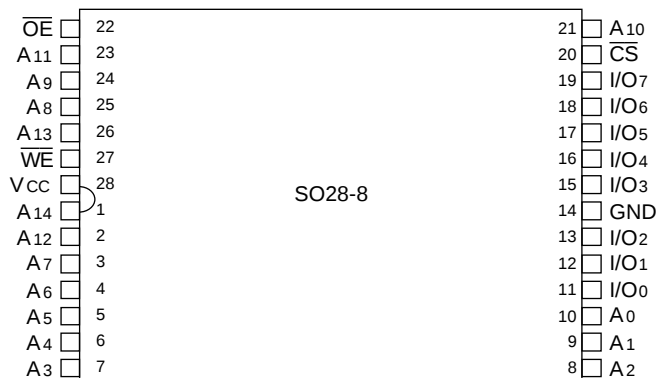
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PIN CONFIGURATIONS



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DIP/SOJ
TOP VIEW



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TSOP
TOP VIEW

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	4.5V to 5.5V
Industrial	-40°C to +85°C	0V	4.5V to 5.5V

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DC ELECTRICAL CHARACTERISTICS

Vcc = 5.0V ± 10%

Symbol	Parameter	Test Condition	IDT71256SA		Unit
			Min.	Max.	
I _{Li}	Input Leakage Current	Vcc = Max., V _{IN} = GND to Vcc	—	5	μA
I _{Lo}	Output Leakage Current	Vcc = Max., CS = V _{IH} , V _{OUT} = GND to Vcc	—	5	μA
V _{OL}	Output Low Voltage	I _{OL} = 8mA, Vcc = Min.	—	0.4	V
V _{OH}	Output High Voltage	I _{OH} = -4mA, Vcc = Min.	2.4	—	V

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ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Value	Unit
Vcc	Supply Voltage Relative to GND	-0.5 to +7.0	V
V _{TERM}	Terminal Voltage Relative to GND	-0.5 to Vcc+0.5	V
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
T _{STG}	Storage Temperature	-55 to +125	°C
P _T	Power Dissipation	1.0	W
I _{OUT}	DC Output Current	50	mA

NOTES:

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- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

TRUTH TABLE^(1,2)

CS	OE	WE	I/O	Function
L	L	H	DATA _{OUT}	Read Data
L	X	L	DATA _{IN}	Write Data
L	H	H	High-Z	Outputs Disabled
H	X	X	High-Z	Deselected — Standby (I _{SB})
V _{HC} ⁽³⁾	X	X	High-Z	Deselected — Standby (I _{SB1})

NOTES:

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- H = V_{IH}, L = V_{IL}, X = Don't care.
- V_{LC} = 0.2V, V_{HC} = Vcc - 0.2V.
- Other inputs ≥ V_{HC} or ≤ V_{LC}.

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V _{IH}	Input High Voltage	2.2	—	Vcc+0.5	V
V _{IL}	Input Low Voltage	-0.5 ⁽¹⁾	—	0.8	V

NOTE:

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- V_{IL} (min.) = -1.5V for pulse width less than 10ns, once per cycle.

DC ELECTRICAL CHARACTERISTICS⁽¹⁾

($V_{CC} = 5.0V \pm 10\%$, $V_{LC} = 0.2V$, $V_{HC} = V_{CC} - 0.2V$)

Symbol	Parameter	71256SA12 ⁽³⁾	71256SA15	71256SA20	71256SA25 ⁽³⁾	Unit
I _{CC}	Dynamic Operating Current $\overline{CS} \leq V_{IL}$, Outputs Open, $V_{CC} = \text{Max.}$, $f = f_{\text{MAX}}$ ⁽²⁾	160	150	145	145	mA
I _{SB}	Standby Power Supply Current (TTL Level) $\overline{CS} \geq V_{IH}$, Outputs Open, $V_{CC} = \text{Max.}$, $f = f_{\text{MAX}}$ ⁽²⁾	50	40	40	40	mA
I _{SB1}	Standby Power Supply Current (CMOS Level) $\overline{CS} \geq V_{HC}$, Outputs Open, $V_{CC} = \text{Max.}$, $f = 0$ ⁽²⁾ $V_{IN} \leq V_{LC}$ or $V_{IN} \geq V_{HC}$	15	15	15	15	mA

NOTES:

- All values are maximum guaranteed values.
- $f_{\text{MAX}} = 1/t_{\text{RC}}$ (all address inputs are cycling at f_{MAX}); $f = 0$ means no address input lines are changing.
- Commercial temperature range only.

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AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figures 1 and 2

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CAPACITANCE

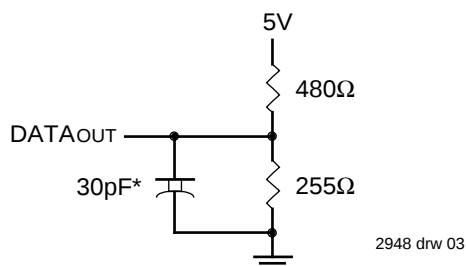
($T_A = +25^\circ\text{C}$, $f = 1.0\text{MHz}$, SOJ package)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
C _{IN}	Input Capacitance	$V_{IN} = 3\text{dV}$	7	pF
C _{I/O}	I/O Capacitance	$V_{OUT} = 3\text{dV}$	7	pF

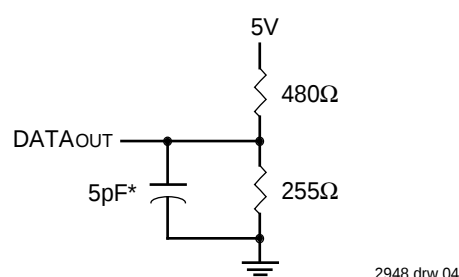
NOTE:

- This parameter is guaranteed by device characterization, but not production tested.

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*Including jig and scope capacitance.

Figure 1. AC Test Load

Figure 2. AC Test Load
(for t_{CLZ}, t_{OLZ}, t_{CHZ}, t_{OHZ}, t_{OW}, and t_{WHZ})

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0V ± 10%)

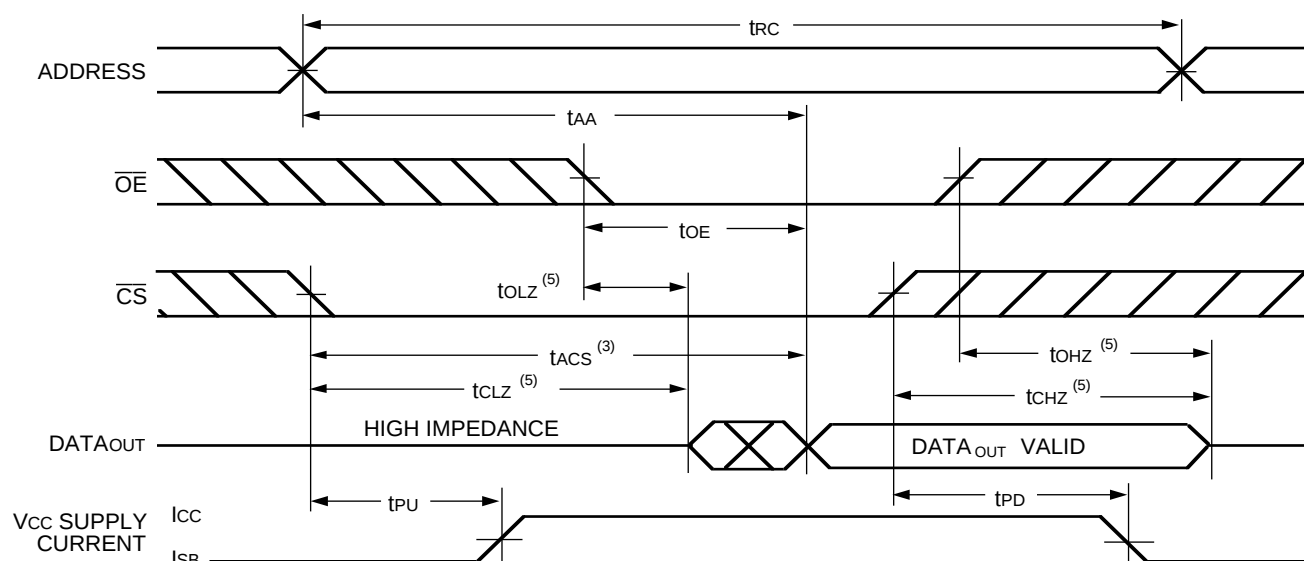
Symbol	Parameter	71256SA12 ⁽²⁾		71256SA15		71256SA20		71256SA25 ⁽²⁾		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
tRC	Read Cycle Time	12	—	15	—	20	—	25	—	ns
tAA	Address Access Time	—	12	—	15	—	20	—	25	ns
tACS	Chip Select Access Time	—	12	—	15	—	20	—	25	ns
tCLZ ⁽¹⁾	Chip Select to Output in Low-Z	4	—	4	—	4	—	4	—	ns
tCHZ ⁽¹⁾	Chip Deselect to Output in High-Z	0	6	0	7	0	10	0	11	ns
tOE	Output Enable to Output Valid	—	6	—	7	—	10	—	11	ns
tOLZ ⁽¹⁾	Output Enable to Output in Low-Z	0	—	0	—	0	—	0	—	ns
tOHZ ⁽¹⁾	Output Disable to Output in High-Z	0	6	0	6	0	8	0	10	ns
tOH	Output Hold from Address Change	3	—	3	—	3	—	3	—	ns
tPU ⁽¹⁾	Chip Select to Power Up Time	0	—	0	—	0	—	0	—	ns
tPD ⁽¹⁾	Chip Deselect to Power Down Time	—	12	—	15	—	20	—	25	ns
Write Cycle										
tWC	Write Cycle Time	12	—	15	—	20	—	25	—	ns
tAW	Address Valid to End of Write	9	—	10	—	15	—	20	—	ns
tCW	Chip Select to End of Write	9	—	10	—	15	—	20	—	ns
tAS	Address Set-up Time	0	—	0	—	0	—	0	—	ns
tWP	Write Pulse Width	9	—	10	—	15	—	20	—	ns
tWR	Write Recovery Time	0	—	0	—	0	—	0	—	ns
tdW	Data Valid to End of Write	6	—	7	—	11	—	13	—	ns
tdH	Data Hold Time	0	—	0	—	0	—	0	—	ns
tOW ⁽¹⁾	Output Active from End of Write	4	—	4	—	4	—	4	—	ns
tWHZ ⁽¹⁾	Write Enable to Output in High-Z	0	6	0	6	0	10	0	11	ns

NOTE:

1. This parameter is guaranteed with the AC Load (Figure 2) by device characterization, but is not production tested.
2. Commercial temperature range only.

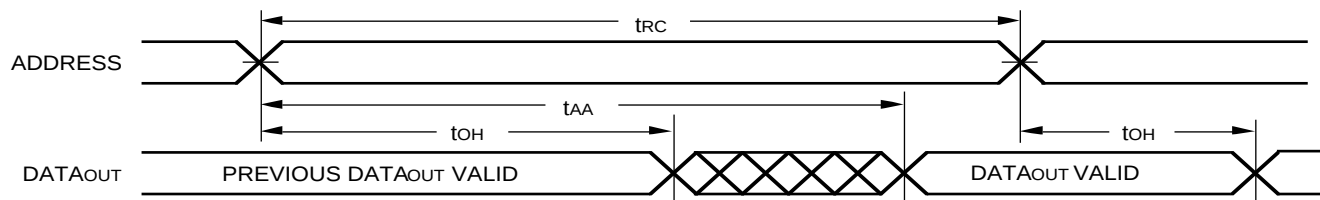
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TIMING WAVEFORM OF READ CYCLE NO. 1⁽¹⁾



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TIMING WAVEFORM OF READ CYCLE NO. 2^(1,2,4)

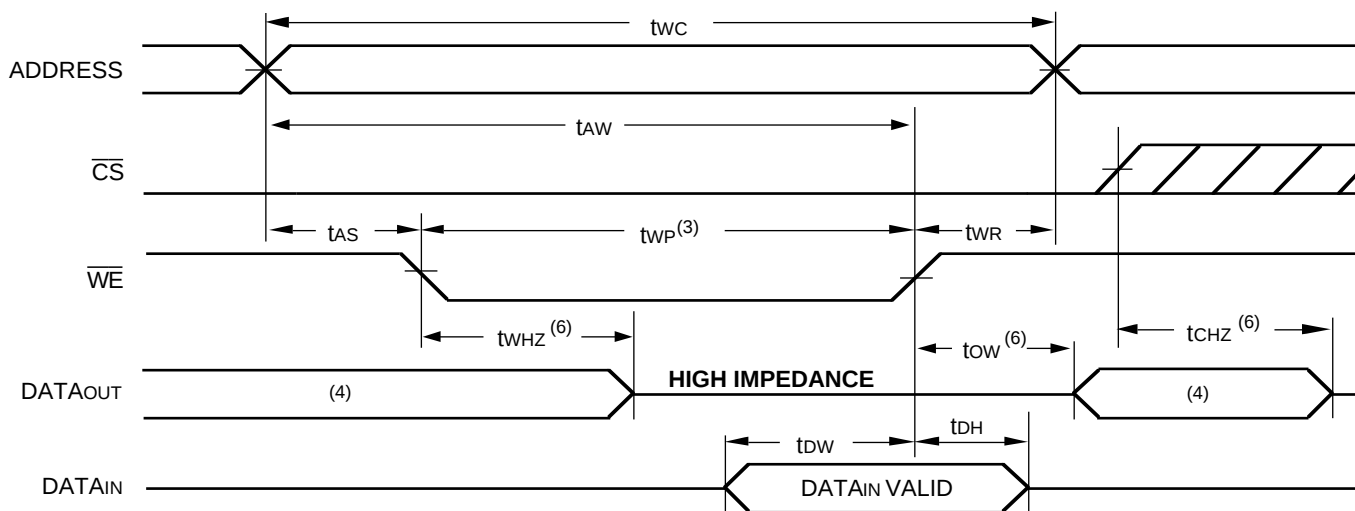


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NOTES:

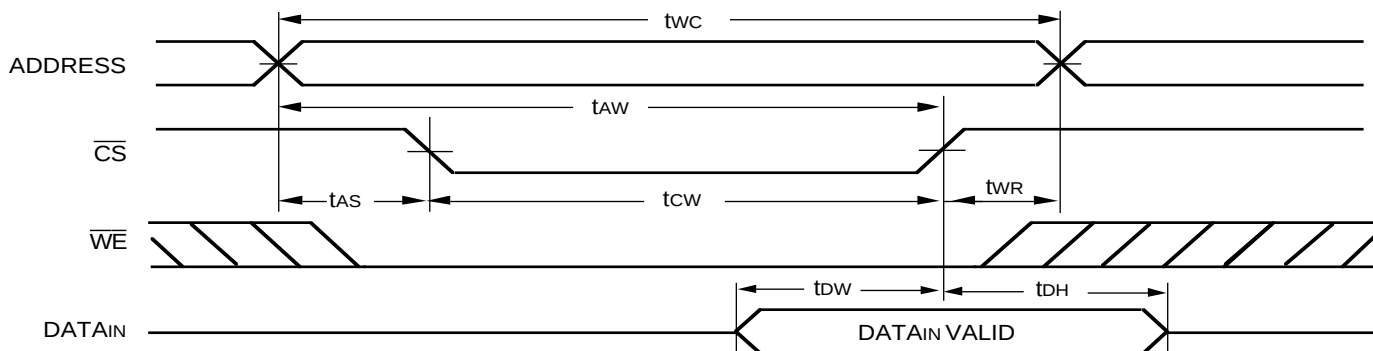
1. $\overline{WE}$ is HIGH for Read Cycle.
2. Device is continuously selected, $\overline{CS}$ is LOW.
3. Address must be valid prior to or coincident with the later of $\overline{CS}$ transition LOW; otherwise t_{AA} is the limiting parameter.
4. $\overline{OE}$ is LOW.
5. Transition is measured $\pm 200\text{mV}$ from steady state.

TIMING WAVEFORM OF WRITE CYCLE NO.1 ($\overline{WE}$ CONTROLLED TIMING)^(1,2,3,5)



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TIMING WAVEFORM OF WRITE CYCLE NO.2 ($\overline{CS}$ CONTROLLED TIMING)^(1,2,5)

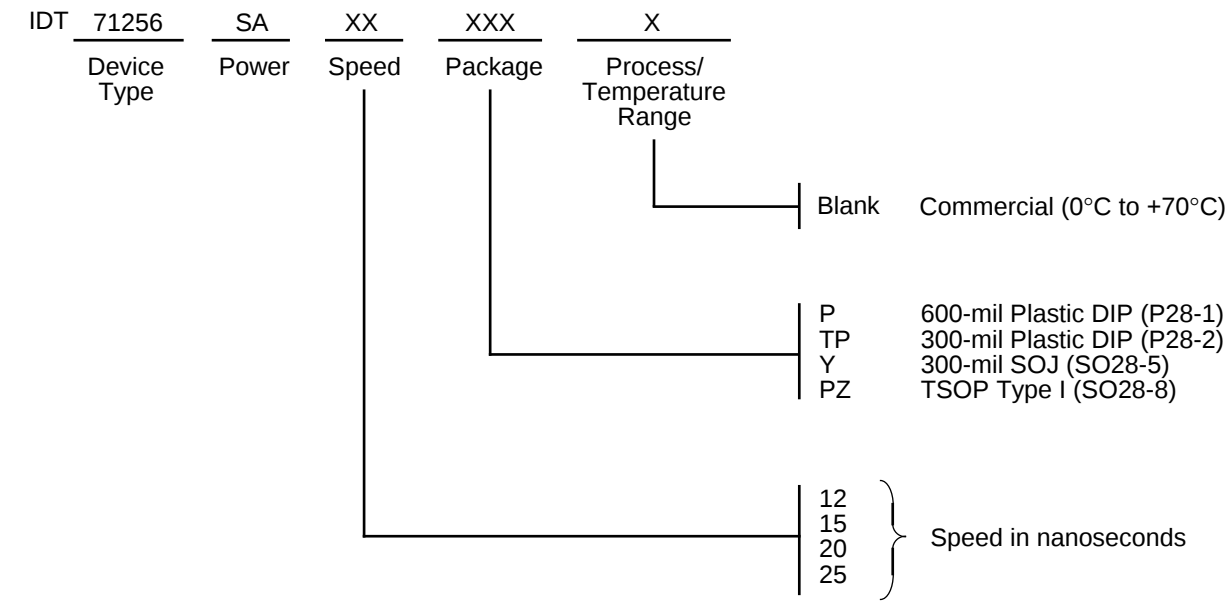


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NOTES:

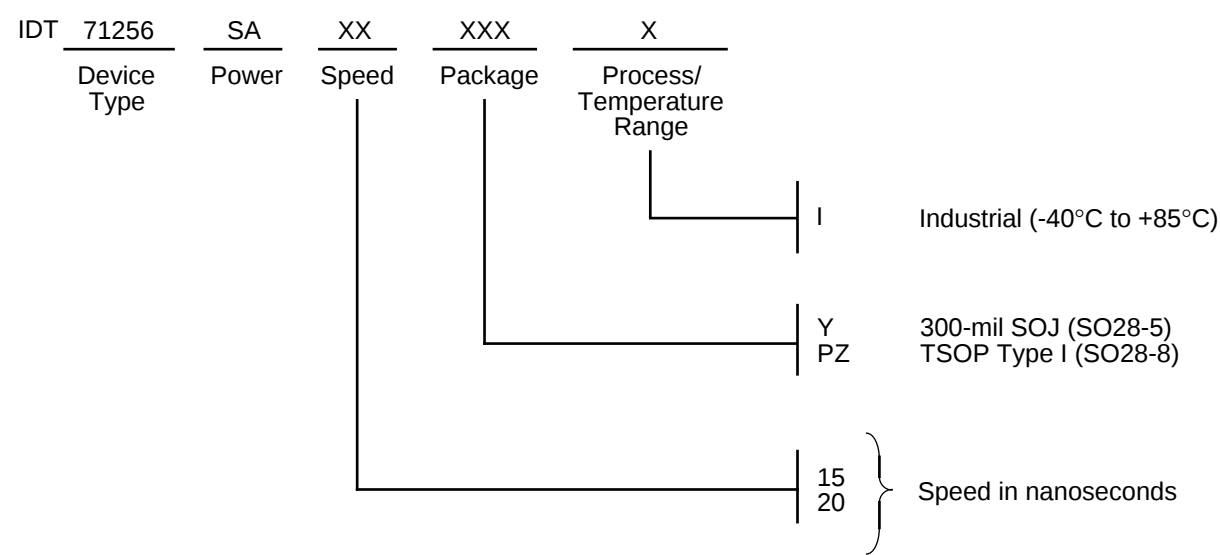
1. $\overline{WE}$ or $\overline{CS}$ must be HIGH during all address transitions.
2. A write occurs during the overlap of a LOW $\overline{CS}$ and a LOW $\overline{WE}$.
3. $\overline{OE}$ is continuously HIGH. If during a $\overline{WE}$ controlled write cycle $\overline{OE}$ is LOW, t_{WP} must be greater than or equal to $t_{WHZ} + t_{DW}$ to allow the I/O drivers to turn off and data to be placed on the bus for the required t_{DW} . If $\overline{OE}$ is HIGH during a $\overline{WE}$ controlled write cycle, this requirement does not apply and the minimum write pulse is as short as the specified t_{WP} .
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CS}$ LOW transition occurs simultaneously with or after the $\overline{WE}$ LOW transition, the outputs remain in a high-impedance state.
6. Transition is measured $\pm 200\text{mV}$ from steady state.

ORDERING INFORMATION - COMMERCIAL



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ORDERING INFORMATION - INDUSTRIAL



2948 drw 10